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H. H. H.
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In re Patent Application of)
Shunpei YAMAZAKI et al.)
Serial No. 09/916,484)
Filed: July 30, 2001)
For: ELECTRIC DEVICE, MATRIX)
DEVICE, ELECTRO-OPTICAL DISPLAY)
DEVICE, AND SEMICONDUCTOR)
MEMORY HAVING THIN-FILM)
TRANSISTORS)

Art Unit: 2823
Examiner: S. Foong

CERTIFICATE OF MAILING

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AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated February 14, 2002 please amend the
above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 1, 7 and 13 and amend claims 2-6, 8-12 and 14-19 as
follows:

2. (Amended) A method according to claim 3, further comprising:
forming a blocking film between the substrate and the semiconductor island,
wherein the substrate is a glass substrate;
wherein the blocking film includes,
a silicon nitride film with a thickness in a range of 5-200 nm formed on the
glass substrate, and
a silicon oxide film with a thickness in a range of 20-1000 nm formed on the
silicon nitride film.